

## R-C Thermal Model Parameters

### DESCRIPTION

The parametric values in the R-C thermal model have been derived using curve-fitting techniques. These techniques are described in "[A Simple Method of Generating Thermal Models for a Power MOSFET](#)"[1]. When implemented in P-Spice, these values have matching characteristic curves to the Single Pulse Transient Thermal Impedance curves for the MOSFET.

R-C values for the electrical circuit in the Foster/Tank and Cauer/Filter configurations are included.

*Note:*

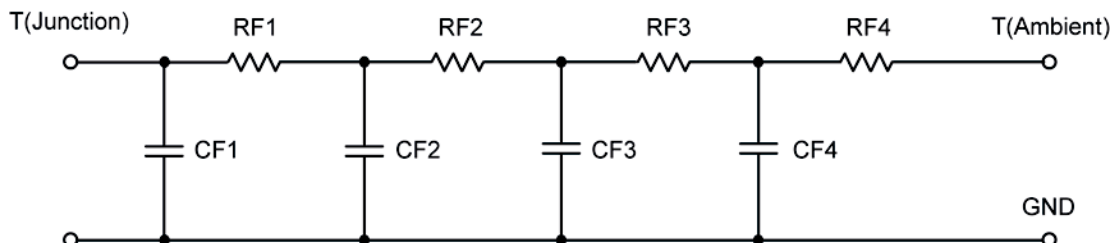
*For a detailed explanation of implementing these values in P-SPICE, refer to [Application Note AN609 Thermal Simulations Of Power MOSFETs on P-SPICE Platform](#).*

### R-C THERMAL MODEL FOR TANK CONFIGURATION



<b>R-C VALUES FOR TANK CONFIGURATION</b>			
Thermal Resistance (°C/W)			
Junction to	Ambient N-Ch	Ambient P-Ch	Foot
RT1	60.4623	58.6690	N/A
RT2	14.9411	15.6129	N/A
RT3	54.7341	55.2668	N/A
RT4	49.8625	50.4513	N/A
Thermal Capacitance (Joules/°C)			
Junction to	Ambient N-Ch	Ambient P-Ch	Foot
CT1	1.8243	1.7313	N/A
CT2	3.0726 m	2.8719 m	N/A
CT3	25.5429 m	27.1470 m	N/A
CT4	9.3817 m	9.7781 m	N/A

*This document is intended as a SPICE modeling guideline and does not constitute a commercial product data sheet. Designers should refer to the appropriate data sheet of the same number for guaranteed specification limits.*

**R-C THERMAL MODEL FOR FILTER CONFIGURATION****R-C VALUES FOR FILTER CONFIGURATION**

Thermal Resistance ( $^{\circ}\text{C}/\text{W}$ )			
Junction to	Ambient N-Ch	Ambient P-Ch	Foot
RF1	33.8072	33.8999	N/A
RF2	50.0899	51.7753	N/A
RF3	37.6983	36.4067	N/A
RF4	58.4046	57.9181	N/A
Thermal Capacitance (Joules/ $^{\circ}\text{C}$ )			
Junction to	Ambient N-Ch	Ambient P-Ch	Foot
CF1	2.4404 m	2.3628 m	N/A
CF2	4.8011 m	5.4969 m	N/A
CF3	23.0576 m	19.8405 m	N/A
CF4	1.8984	1.7328	N/A

Note: NA indicates not applicable

Reference:

[1] "A Simple Method of Generating Thermal Models for a Power MOSFET" by Wharton McDaniel and Kandarp Pandya. IEEE / SEMITHERM 2002

